

IN THE SPECIFICATION:

Please amend paragraphs [0097] and [0100] in the specification as follows:

[0097] The accumulation layer 8 is formed on the entire back surface side of the n-type silicon substrate 43 [[3]]. The AR film 24 is formed on the accumulation layer 8. This accumulation layer 8 and the AR film 24 are similar to those in the aforementioned photodiode array 1. The aforementioned spacers 6 are provided in the noncorresponding region of each photodiode 4 on the AR film 24. The spacers 6 are also similar to those in the aforementioned photodiode array 1.

[0100] The accumulation layer 8 permits the carriers generated near the light-incident surface (back surface) inside the n-type silicon substrate 43 [[3]] to efficiently migrate to the pn junctions, without recombination. This permits the photodiode array 41 to have higher photodetecting sensitivity (though the photodiode array 41 of the present embodiment has the detection sensitivity at a practically acceptable level, without provision of the accumulation layer 8).